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#### What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

#### Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	36MHz
Connectivity	I <sup>2</sup> C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	37
Program Memory Size	128KB (128K × 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16К х 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f101cbt6tr

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

# 1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32F101x8 and STM32F101xB medium-density access line microcontrollers. For more details on the whole STMicroelectronics STM32F101xx family, please refer to *Section 2.2: Full compatibility throughout the family*.

The medium-density STM32F101xx datasheet should be read in conjunction with the low-, medium- and high-density STM32F10xxx reference manual. For information on programming, erasing and protection of the internal Flash memory please refer to the *STM32F10xxx Flash programming manual*. The reference and Flash programming manuals are both available from the STMicroelectronics website *www.st.com*.

For information on the Cortex<sup>®</sup> -M3 core please refer to the Cortex<sup>®</sup> -M3 Technical Reference Manual, available from the www.arm.com website.





# 2.2 Full compatibility throughout the family

The STM32F101xx is a complete family whose members are fully pin-to-pin, software and feature compatible. In the reference manual, the STM32F101x4 and STM32F101x6 are referred to as low-density devices, the STM32F101x8 and STM32F101xB are referred to as medium-density devices, and the STM32F101xC, STM32F101xD and STM32F101xE are referred to as high-density devices.

Low- and high-density devices are an extension of the STM32F101x8/B devices, they are specified in the STM32F101x4/6 and STM32F101xC/D/E datasheets, respectively. Low-density devices feature lower Flash memory and RAM capacities and a timer less. High-density devices have higher Flash memory and RAM capacities, and additional peripherals like FSMC and DAC, while remaining fully compatible with the other members of the STM32F101xx family.

The STM32F101x4, STM32F101x6, STM32F101xC, STM32F101xD and STM32F101xE are a drop-in replacement for the STM32F101x8/B medium-density devices, allowing the user to try different memory densities and providing a greater degree of freedom during the development cycle.

Moreover, the STM32F101xx performance line family is fully compatible with all existing STM32F101xx access line and STM32F102xx USB access line devices.

				Memory size	ļ			
	Low-density devices		Medium-density devices		High-density devices			
Pinout	16 KB Flash	32 KB Flash <sup>(1)</sup>	64 KB Flash	128 KB Flash	256 KB Flash	384 KB Flash	512 KB Flash	
	4 KB RAM 6 KB RAM		10 KB RAM 16 KB RAM		32 KB RAM	48 KB RAM	48 KB RAM	
144	-	-	-	-	5 × USARTs			
100	-	-			4 × 16-bit tin 3 × SPIs, 2 ×	ners, 2 × basi < I <sup>2</sup> Cs, 1 × A[	ic timers DC,	
64	2 × USART	s	3 × 16-bit tim	ers	2 × DACs, FSMC (100 and 14		nd 144 pins)	
48	2 × 16-bit tii 1 × SPI, 1 ×	mers ‹ I <sup>2</sup> C	2 × SPIs, 2 ×	I2Cs,	-	-	-	
36	1 × ADC				-	-	-	

Table 3. STM32F101xx family

1. For orderable part numbers that do not show the A internal code after the temperature range code (6), the reference datasheet for electrical characteristics is that of the STM32F101x8/B medium-density devices.



### 2.3.13 DMA

The flexible 7-channel general-purpose DMA is able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. The DMA controller supports circular buffer management avoiding the generation of interrupts when the controller reaches the end of the buffer.

Each channel is connected to dedicated hardware DMA requests, with support for software trigger on each channel. Configuration is made by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals: SPI,  $I^2C$ , USART, general purpose timers TIMx and ADC.

#### 2.3.14 RTC (real-time clock) and backup registers

The RTC and the backup registers are supplied through a switch that takes power either on  $V_{DD}$  supply when present or through the  $V_{BAT}$  pin. The backup registers are ten 16-bit registers used to store 20 bytes of user application data when  $V_{DD}$  power is not present.

The real-time clock provides a set of continuously running counters which can be used with suitable software to provide a clock calendar function, and provides an alarm interrupt and a periodic interrupt. It is clocked by a 32.768 kHz external crystal, resonator or oscillator, the internal low power RC oscillator or the high-speed external clock divided by 128. The internal low power RC has a typical frequency of 40 kHz. The RTC can be calibrated using an external 512 Hz output to compensate for any natural crystal deviation. The RTC features a 32-bit programmable counter for long term measurement using the Compare register to generate an alarm. A 20-bit prescaler is used for the time base clock and is by default configured to generate a time base of 1 second from a clock at 32.768 kHz.

#### 2.3.15 Independent watchdog

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 40 kHz internal RC and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used as a watchdog to reset the device when a problem occurs, or as a free running timer for application timeout management. It is hardware or software configurable through the option bytes. The counter can be frozen in debug mode.

### 2.3.16 Window watchdog

The window watchdog is based on a 7-bit downcounter that can be set as free running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.



#### 2.3.17 SysTick timer

This timer is dedicated for OS, but could also be used as a standard down counter. It features:

- A 24-bit down counter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0.
- Programmable clock source

#### 2.3.18 General-purpose timers (TIMx)

There are three synchronizable general-purpose timers embedded in the STM32F101xx medium-density access line devices. These timers are based on a 16-bit auto-reload up/down counter, a 16-bit prescaler and feature 4 independent channels each for input capture, output compare, PWM or one pulse mode output. This gives up to 12 input captures / output compares / PWMs on the largest packages.

The general-purpose timers can work together via the Timer Link feature for synchronization or event chaining. Their counter can be frozen in debug mode. Any of the general-purpose timers can be used to generate PWM outputs. They all have independent DMA request generation.

These timers are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

## 2.3.19 I<sup>2</sup>C bus

Up to two I<sup>2</sup>C bus interfaces can operate in multimaster and slave modes. They can support standard and fast modes.

They support dual slave addressing (7-bit only) and both 7/10-bit addressing in master mode. A hardware CRC generation/verification is embedded. They can be served by DMA and they support SM Bus 2.0/PM Bus.

#### 2.3.20 Universal synchronous/asynchronous receiver transmitter (USART)

The available USART interfaces communicate at up to 2.25 Mbit/s. They provide hardware management of the CTS and RTS signals, support IrDA SIR ENDEC, are ISO 7816 compliant and have LIN Master/Slave capability.

The USART interfaces can be served by the DMA controller.

#### 2.3.21 Serial peripheral interface (SPI)

Up to two SPIs are able to communicate up to 18 Mbit/s in slave and master modes in fullduplex and simplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes.

Both SPIs can be served by the DMA controller.

#### 2.3.22 GPIOs (general-purpose inputs/outputs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the



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	Pir	าร						Alternate function	ons <sup>(3)(4)</sup>
LQFP48/ UFQFPN48	LQFP64	LQFP100	VFQFPN36	Pin name	Type <sup>(1)</sup>	I / O level <sup>(2)</sup>	Main function <sup>(3)</sup> (after reset)	Default	Remap
-	-	1	-	PE2	I/O	FT	PE2	TRACECLK	-
-	-	2	-	PE3	I/O	FT	PE3	TRACED0	-
-	-	3	-	PE4	I/O	FT	PE4	TRACED1	-
-	-	4	-	PE5	I/O	FT	PE5	TRACED2	-
-	-	5	-	PE6	I/O	FT	PE6	TRACED3	-
1	1	6	-	V <sub>BAT</sub>	S	-	V <sub>BAT</sub>	-	-
2	2	7	-	PC13-TAMPER- RTC <sup>(5)</sup>	I/O	-	PC13 <sup>(6)</sup>	TAMPER-RTC	-
3	3	8	-	PC14- OSC32_IN <sup>(5)</sup>	I/O	-	PC14 <sup>(6)</sup>	OSC32_IN	-
4	4	9	-	PC15- OSC32_OUT <sup>(5)</sup>	I/O	-	PC15 <sup>(6)</sup>	OSC32_OUT	-
-	-	10	-	V <sub>SS_5</sub>	S	-	$V_{SS_5}$	-	-
-	-	11	-	V <sub>DD_5</sub>	S	-	$V_{DD_5}$	-	-
5	5	12	2	OSC_IN	Ι	-	OSC_IN	-	PD0 <sup>(7)</sup>
6	6	13	3	OSC_OUT	0	-	OSC_OUT	-	PD1 <sup>(7)</sup>
7	7	14	4	NRST	I/O	-	NRST	-	-
-	8	15	-	PC0	I/O	-	PC0	ADC_IN10	-
-	9	16	-	PC1	I/O	-	PC1	ADC_IN11	-
-	10	17	-	PC2	I/O	-	PC2	ADC_IN12	-
-	11	18	-	PC3	I/O	-	PC3	ADC_IN13	-
8	12	19	5	V <sub>SSA</sub>	S	-	V <sub>SSA</sub>	-	-
-	-	20	-	V <sub>REF-</sub>	S	-	V <sub>REF-</sub>	-	-
-	-	21	-	V <sub>REF+</sub>	S	-	V <sub>REF+</sub>	-	-
9	13	22	6	V <sub>DDA</sub>	S	-	V <sub>DDA</sub>	-	-
10	14	23	7	PA0-WKUP	I/O	-	PA0	WKUP/USART2_CTS <sup>(8)</sup> / ADC_IN0/ TIM2_CH1_ETR <sup>(8)</sup>	-
11	15	24	8	PA1	I/O	-	PA1	USART2_RTS <sup>(8)</sup> / ADC_IN1/TIM2_CH2 <sup>(8)</sup>	-

Table 4. Medium-density STM32F101xx pin definitions



Symbol	Parameter	Conditions		Min	Max	Unit
		Standard	10	-0.3	V <sub>DD</sub> + 0.3	
V		ET 10 <sup>(3)</sup>	$2~V < V_{DD} \leq 3.6~V$	-0.3	5.5	
۷IN	I/O Input voltage		V <sub>DD</sub> = 2 V	-0.3	5.2	v
		BOOT0		0	5.5	
		LQFP100		-	434	mW
	Power dissipation at $T_A = 85 °C$	LQFP64		-	444	
$P_{D}$		LQFP48		-	363	
		UFQFPN48		-	624	
		VFQFPN36		-	1000	
T. Ambient termenture		Maximum power dissipation		-40	85	
IA		Low power dissipation <sup>(5)</sup>		-40	105	°C
TJ	Junction temperature range		-	-40	105	

 Table 8. General operating conditions (continued)

1. When the ADC is used, refer to *Table 41: ADC characteristics*.

2. It is recommended to power V<sub>DD</sub> and V<sub>DDA</sub> from the same source. A maximum difference of 300 mV between V<sub>DD</sub> and V<sub>DDA</sub> can be tolerated during power-up and operation.

- 3. To sustain a voltage higher than  $V_{DD}$ +0.3 V, the internal pull-up/pull-down resistors must be disabled.
- If T<sub>A</sub> is lower, higher P<sub>D</sub> values are allowed as long as T<sub>J</sub> does not exceed T<sub>J</sub>max (see Table 6.7: Thermal characteristics on page 90).
- In low power dissipation state, T<sub>A</sub> can be extended to this range as long as T<sub>J</sub> does not exceed T<sub>J</sub>max (see Table 6.7: Thermal characteristics on page 90).

### 5.3.2 Operating conditions at power-up / power-down

Subject to general operating conditions for T<sub>A</sub>.

Table 9. Operating	conditions at p	oower-up /	power-down
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Symbol	Parameter	Conditions	Min	Мах	Unit
+	V <sub>DD</sub> rise time rate		0	8	4004
٩VDD	V <sub>DD</sub> fall time rate	-	20	8	μ5/ ν

#### 5.3.3 Embedded reset and power control block characteristics

The parameters given in *Table 10* are derived from tests performed under the ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 8*.



The test results are given in *Table 28*. They are based on the EMS levels and classes defined in application note AN1709.

Symbol	Parameter	Conditions	Level/Class
V <sub>FESD</sub>	Voltage limits to be applied on any I/O pin to induce a functional disturbance	$V_{DD} = 3.3 \text{ V},  \text{T}_{\text{A}} = +25 ^{\circ}\text{C}, \\ \text{f}_{\text{HCLK}} = 36 \text{ MHz} \\ \text{conforms to IEC 61000-4-2} \\ \end{array}$	2B
V <sub>EFTB</sub>	Fast transient voltage burst limits to be applied through 100 pF on $V_{DD}$ and $V_{SS}$ pins to induce a functional disturbance	$\label{eq:VDD} \begin{array}{l} V_{DD} = 3.3 \text{ V},  \text{T}_{\text{A}} = +25 \ ^{\circ}\text{C}, \\ \text{f}_{\text{HCLK}} = 36 \ \text{MHz} \\ \text{conforms to IEC 61000-4-4} \end{array}$	4A

#### Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and pre qualification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

#### **Prequalification trials**

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second. To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

#### **Electromagnetic Interference (EMI)**

The electromagnetic field emitted by the device is monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC61967-2 standard which specifies the test board and the pin loading.

Symbol Parameter		Conditions	Monitored	Max vs. [f <sub>HSE</sub> /f <sub>HCLK</sub> ]	Unit	
Cymbol		Conditione	frequency band	8/36 MHz	•	
S <sub>EMI</sub> Peak level		0.1 MHz to 30 MHz	7			
	Peak level	eak level LQFP100 package compliant with IEC 61967-2	30 MHz to 130 MHz	8	dBµV	
	reak level		130 MHz to 1GHz	13		
			SAE EMI Level	3.5	-	

Table	29	FMI	chara	cter	istics
Table	<b>Z</b> J.		unara	CLEI	いっこしつ



All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements is shown in *Figure 23* and *Figure 24* for standard I/Os, and in *Figure 25* and *Figure 26* for 5 V tolerant I/Os.



Figure 23. Standard I/O input characteristics - CMOS port









Figure 25. 5 V tolerant I/O input characteristics - CMOS port









#### Figure 27. I/O AC characteristics definition

#### 5.3.14 **NRST** pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R<sub>PU</sub> (see Table 33).

Unless otherwise specified, the parameters given in Table 36 are derived from tests performed under the ambient temperature and V<sub>DD</sub> supply voltage conditions summarized in Table 8.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>IL(NRST)</sub> <sup>(1)</sup>	NRST Input low level voltage	-	-0.5	-	0.8	V
V <sub>IH(NRST)</sub> <sup>(1)</sup>	NRST Input high level voltage	-	2	-	V <sub>DD</sub> +0.5	v
V <sub>hys(NRST)</sub>	NRST Schmitt trigger voltage hysteresis	-	-	200	-	mV
R <sub>PU</sub>	Weak pull-up equivalent resistor <sup>(2)</sup>	$V_{IN} = V_{SS}$	30	40	50	kΩ
V <sub>F(NRST)</sub> <sup>(1)</sup>	NRST Input filtered pulse	-	-	-	100	ns
V <sub>NF(NRST)</sub> <sup>(1)</sup>	NRST Input not filtered pulse	-	300	-	-	ns

Table 36. NRST pin characteristics

1. Guaranteed by design, not tested in production.

The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to 2. the series resistance must be minimum (~10% order).





Figure 28. Recommended NRST pin protection

1. The reset network protects the device against parasitic resets.

2. The user must ensure that the level on the NRST pin can go below the  $V_{IL(NRST)}$  max level specified in *Table 36*. Otherwise the reset will not be taken into account by the device.





Figure 29. I<sup>2</sup>C bus AC waveforms and measurement circuit<sup>(1)</sup>

1. Measurement points are done at CMOS levels:  $0.3V_{\text{DD}}$  and  $0.7V_{\text{DD}}$ 

2. Rs = Series protection resistors, Rp = Pull-up resistors,  $V_{DD \ I2C}$  = I2C bus supply.

f (ku-)	I2C_CCR value
	R <sub>P</sub> = 4.7 kΩ
400	0x801E
300	0x8028
200	0x803C
100	0x00B4
50	0x0168
20	0x0384

### Table 39. SCL frequency ( $f_{PCLK1}$ = 36 MHz, $V_{DD_{-12C}}$ = 3.3 V)<sup>(1)(2)</sup>

1.  $R_P$  = External pull-up resistance,  $f_{SCL}$  =  $I^2C$  speed,

For speeds around 200 kHz, the tolerance on the achieved speed is of ±5%. For other speed ranges, the tolerance on the achieved speed ±2%. These variations depend on the accuracy of the external components used to design the application.



### Equation 1: R<sub>AIN</sub> max formula:

$$R_{AIN} < \frac{\Gamma_{S}}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The formula above (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

T <sub>s</sub> (cycles)	t <sub>S</sub> (μs)	R <sub>AIN</sub> max (kΩ)
1.5	0.11	0.4
7.5	0.54	5.9
13.5	0.96	11.4
28.5	2.04	25.2
41.5	2.96	37.2
55.5	3.96	50
71.5	5.11	NA
239.5	17.1	NA

Table 42. RAIN max f	for $f_{ADC} = 14$	MHz <sup>(1)</sup>
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1. Guaranteed by design, not tested in production.

Symbol	Parameter	Test conditions	Тур	Max <sup>(3)</sup>	Unit
ET	Total unadjusted error	f <sub>PCI K2</sub> = 28 MHz,	±1.3	±2	
EO	Offset error	$f_{ADC} = 14 \text{ MHz}, R_{AIN} < 10 \text{ k}\Omega,$	±1	±1.5	
EG	Gain error	$V_{DDA} = 3 V \text{ to } 3.6 V$ T <sub>A</sub> = 25 °C	±0.5	±1.5	LSB
ED	Differential linearity error	Measurements made after	±0.7	±1	
EL	Integral linearity error	ADC calibration	±0.8	±1.5	

Table 43, ADC accuracy	v - limited test	$conditions^{(1)}$
Table 45. ADO acculac	y - minieu iesi	conditions

1. ADC DC accuracy values are measured after internal calibration.

 ADC Accuracy vs. Negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.

inject negative current. Any positive injection current within the limits specified for  $I_{INJ(PIN)}$  and  $\Sigma I_{INJ(PIN)}$  in Section 5.3.12 does not affect the ADC accuracy.

3. Based on characterization, not tested in production.



Symbol	Parameter	Test conditions	Тур	Max <sup>(4)</sup>	Unit
ET	Total unadjusted error		±2	±5	
EO	Offset error	$f_{ADC} = 14 \text{ MHz}, R_{AIN} < 10 \text{ k}\Omega,$	±1.5	±2.5	
EG	Gain error	$V_{DDA} = 2.4 V \text{ to } 3.6 V$	±1.5	±3	LSB
ED	Differential linearity error	Measurements made after	±1	±2	
EL	Integral linearity error		±1.5	±3	

#### Table 44. ADC accuracy<sup>(1) (2) (3)</sup>

1. ADC DC accuracy values are measured after internal calibration.

2. Better performance could be achieved in restricted  $V_{DD}$ , frequency,  $V_{REF}$  and temperature ranges.

3. ADC Accuracy vs. Negative Injection Current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current. Any positive injection current within the limits specified for I<sub>INJ(PIN)</sub> and ΣI<sub>INJ(PIN)</sub> in Section 5.3.12 does not affect the ADC accuracy.

4. Based on characterization, not tested in production.









Figure 34. Typical connection diagram using the ADC

1. Refer to *Table 41* for the values of  $R_{AIN}$ ,  $R_{ADC}$  and  $C_{ADC}$ .

 C<sub>parasitic</sub> represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high C<sub>parasitic</sub> value will downgrade conversion accuracy. To remedy this, f<sub>ADC</sub> should be reduced.

#### **General PCB design guidelines**

Power supply decoupling should be performed as shown in *Figure 35* or *Figure 36*, depending on whether  $V_{REF+}$  is connected to  $V_{DDA}$  or not. The 10 nF capacitors should be ceramic (good quality). They should be placed them as close as possible to the chip.





<sup>1.</sup>  $V_{REF+}$  and  $V_{REF-}$  inputs are available only on 100-pin packages.





#### Figure 41. VFQFPN36 - 36-pin, 6x6 mm, 0.5 mm pitch very thin profile fine pitch quad flat package recommended footprint

1. Dimensions are expressed in millimeters.



# 6.6 LQFP48 package information

SEATING PLANE С A A ŨŦŨŦŨŦŨŦĬĦŮ<del>Ÿ</del>ŨŦŨŦŨŦŨŦŎŹ ¥ 0.25 mm GAUGE PLANE ĸ D A1 D1 L1 D3 <u>ÅAAAAA AAAAAAA</u> 24 37 Œ b **CHE** E E ш Ē ----------€ 48 13 PIN 1 IDENTIFICATION 1 12 e 5B\_ME\_V2

#### Figure 49. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline

1. Drawing is not to scale.







# 7 Ordering information scheme

Example:	STM32F	101 C 8	T	6	xxx
Device family					
STM32 = ARM-based 32-bit microcontroller					
Product type					
F = general-purpose					
Device subfamily					
101 = access line					
Pin count					
T = 36 pins					
C = 48 pins					
R = 64 pins					
V = 100 pins					
Flash memory size <sup>(1)</sup>					
8 = 64 Kbytes of Flash memory					
B = 128 Kbytes of Flash memory					
Packano					
T = LOFP					
U = VEOFPN or UEOFPN					
Temperature range					
6 = Industrial temperature range, -40 to 85	°C.				
Options					

#### Table 52. Ordering information scheme

xxx = programmed parts

TR = tape and real



<sup>1.</sup> Although STM32F101x6 devices are not described in this datasheet, orderable part numbers that do not show the A internal code after temperature range code 6 should be referred to this datasheet for the electrical characteristics. The low-density datasheet only covers STM32F101x6 devices that feature the A code.

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact the nearest ST sales office.



Date	Revision	Changes
		Figure 2: Clock tree on page 13 added.
		CRC added (see <i>CRC</i> (cyclic redundancy check) calculation unit on page 9 and Figure 8: Memory map on page 29 for address).
		Maximum T <sub>J</sub> value given in <i>Table 7: Thermal characteristics on page</i> 33.
		$P_D$ , $T_A$ and $T_J$ added, $t_{prog}$ values modified and $t_{prog}$ description clarified in <i>Table 27: Flash memory characteristics on page 51</i> .
		I <sub>DD</sub> modified in <i>Table 15: Typical and maximum current consumptions in Stop and Standby modes on page 39.</i>
		ACC <sub>HSI</sub> modified in <i>Table 23: HSI oscillator characteristics on page 49</i> , note 2 removed.
		t <sub>RET</sub> modified in <i>Table 27: Flash memory characteristics</i> .
14-Mar-2008	5	V <sub>NF(NRST)</sub> unit corrected in <i>Table 36: NRST pin characteristics on page 60</i> .
		Table 40: SPI characteristics on page 65 modified.
		I <sub>VREF</sub> added in <i>Table 41: ADC characteristics on page 68.</i>
		Table 43: ADC accuracy - limited test conditions added. Table 44: ADC accuracy modified.
		LQFP100 package specifications updated (see Section 6: Package characteristics on page 73).
		Recommended LQFP100, LQFP64, LQFP48 and VFQFPN36 footprints added (see <i>Figure 44</i> , <i>Figure 47</i> , <i>Figure 50</i> and <i>Figure 41</i> ).
		Section 6.7: Thermal characteristics on page 90 modified.
		Appendix A: Important notes removed.
		Small text changes.
		In Table 27: Flash memory characteristics:
		<ul> <li>N<sub>END</sub> tested over the whole temperature range</li> </ul>
21-Mar-2008	6	<ul> <li>cycling conditions specified for t<sub>RET</sub></li> </ul>
		- t <sub>RET</sub> min modified at T <sub>A</sub> = 55 °C
		Figure 2: Clock tree corrected. Figure 8: Memory map clarified.
		V <sub>25</sub> , Avg_Slope and T <sub>L</sub> modified in <i>Table 45: TS characteristics</i> . CRC feature removed.
22-May-2008	7	Section 1: Introduction modified, Section 2.2: Full compatibility throughout the family added. CRC feature added.
		I <sub>DD_VBAT</sub> removed from <i>Table 21: Typical current consumption in Standby</i> mode on page 42.
		Values added to Table 39: SCL frequency (fPCLK1= 36 MHz, VDD_I2C = 3.3 V) on page 64.
		<i>Figure 30: SPI timing diagram - slave mode and CPHA = 0 on page 66</i> modified. <i>Equation 1</i> corrected.
		Section 6.7.2: Evaluating the maximum junction temperature for an application on page 91 added.
		Axx option added to Table 52: Ordering information scheme on page 92.

Table 53. Document revision history (continued)

